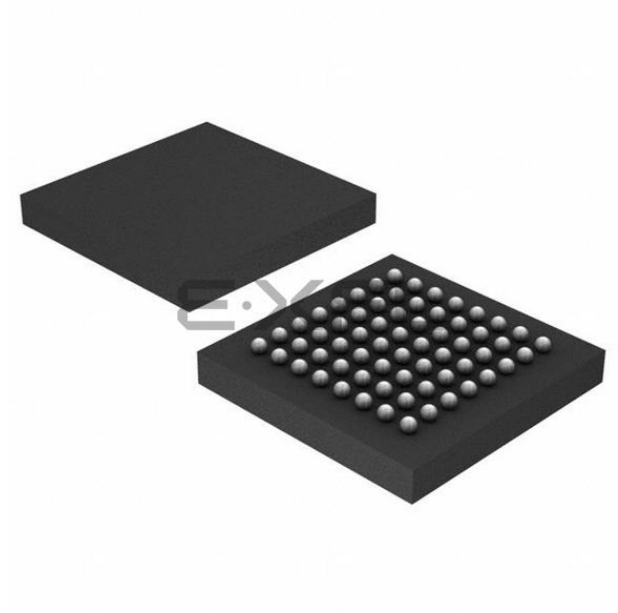


Welcome to E-XFL.COM

What is "Embedded - Microcontrollers"?

"Embedded - Microcontrollers" refer to small, integrated circuits designed to perform specific tasks within larger systems. These microcontrollers are essentially compact computers on a single chip, containing a processor core, memory, and programmable input/output peripherals. They are called "embedded" because they are embedded within electronic devices to control various functions, rather than serving as standalone computers. Microcontrollers are crucial in modern electronics, providing the intelligence and control needed for a wide range of applications.

Applications of "Embedded - Microcontrollers"

Details	
Product Status	Obsolete
Core Processor	ARM7®
Core Size	32-Bit Single-Core
Speed	60MHz
Connectivity	CANbus, I²C, SPI, SSI, SSP, UART/USART
Peripherals	DMA, PWM, WDT
Number of I/O	38
Program Memory Size	256KB (256K x 8)
Program Memory Type	FLASH
EEPROM Size	-
RAM Size	16K x 8
Voltage - Supply (Vcc/Vdd)	3V ~ 5.5V
Data Converters	A/D 11x10b
Oscillator Type	Internal
Operating Temperature	-40°C ~ 105°C (TA)
Mounting Type	Surface Mount
Package / Case	64-LFBGA
Supplier Device Package	-
Purchase URL	https://www.e-xfl.com/product-detail/stmicroelectronics/str752fr2h7

Contents

1 **Description** 4

2 **Device overview** 4

3 **Introduction** 5

3.1 Functional description 5

3.2 Block diagram 11

4 **Pin description** 12

4.1 Pin description table 15

4.2 External components 22

5 **Memory map** 23

6 **Electrical parameters** 24

6.1 Parameter conditions 24

6.1.1 Minimum and maximum values 24

6.1.2 Typical values 24

6.1.3 Typical curves 24

6.1.4 Loading capacitor 25

6.1.5 Pin input voltage 25

6.1.6 Power supply schemes 26

6.1.7 I/O characteristics versus the various power schemes (3.3V or 5.0V) . 29

6.1.8 Current consumption measurements 29

6.2 Absolute maximum ratings 32

6.2.1 Voltage characteristics 32

6.2.2 Current characteristics 33

6.2.3 Thermal characteristics 33

6.3 Operating conditions 34

6.3.1 General operating conditions 34

6.3.2 Operating conditions at power-up / power-down 35

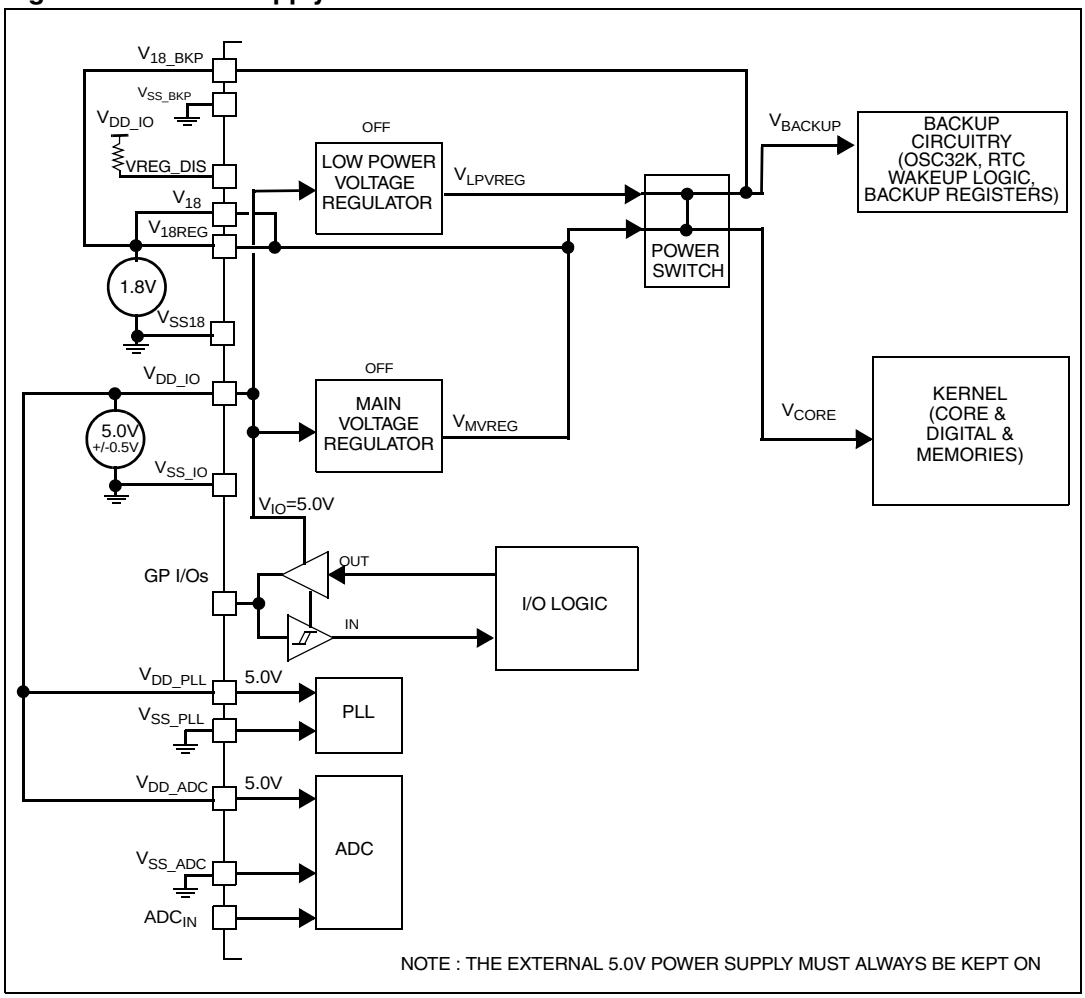
6.3.3 Embedded voltage regulators 35

6.3.4 Supply current characteristics 36

6.3.5 Clock and timing characteristics 44

Power supply scheme 4: Dual external 1.8 V and 5.0 V supply

Figure 11. Power supply scheme 4



6.1.7 I/O characteristics versus the various power schemes (3.3V or 5.0V)

Unless otherwise mentioned, all the I/O characteristics are valid for both

- V_{DD_IO}=3.0 V to 3.6 V with bit EN33=1
- V_{DD_IO}=4.5 V to 5.5 V with bit EN33=0

When V_{DD_IO}=3.0 V to 3.6 V, I/Os are not 5V tolerant.

6.1.8 Current consumption measurements

All the current consumption measurements mentioned below refer to Power scheme 1 and 2 as described in *Figure 12* and *Figure 13*

Figure 12. Power consumption measurements in power scheme 1 (regulators enabled)

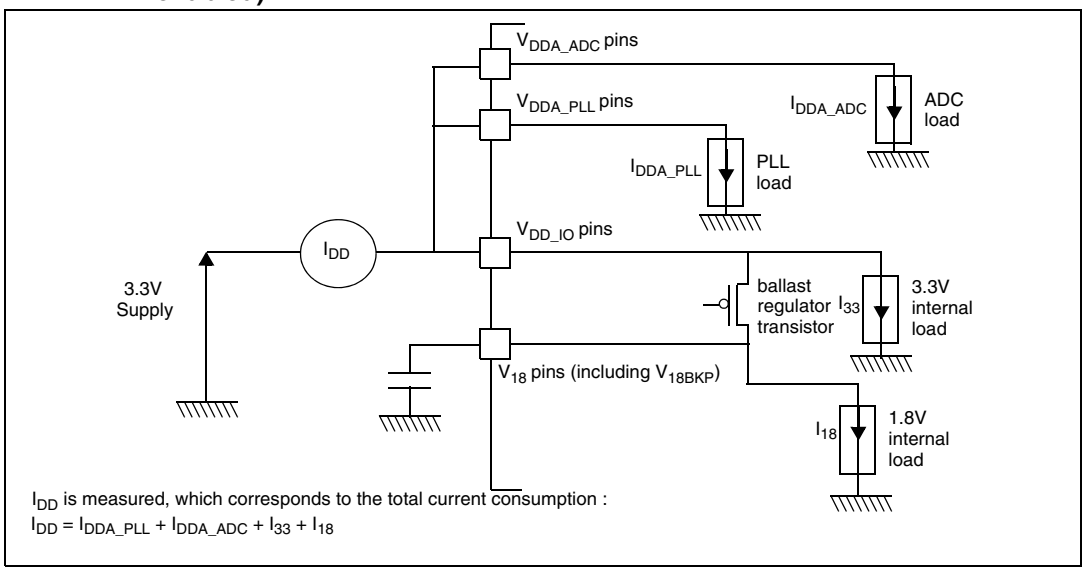


Figure 13. Power consumption measurements in power scheme 2 (regulators disabled)

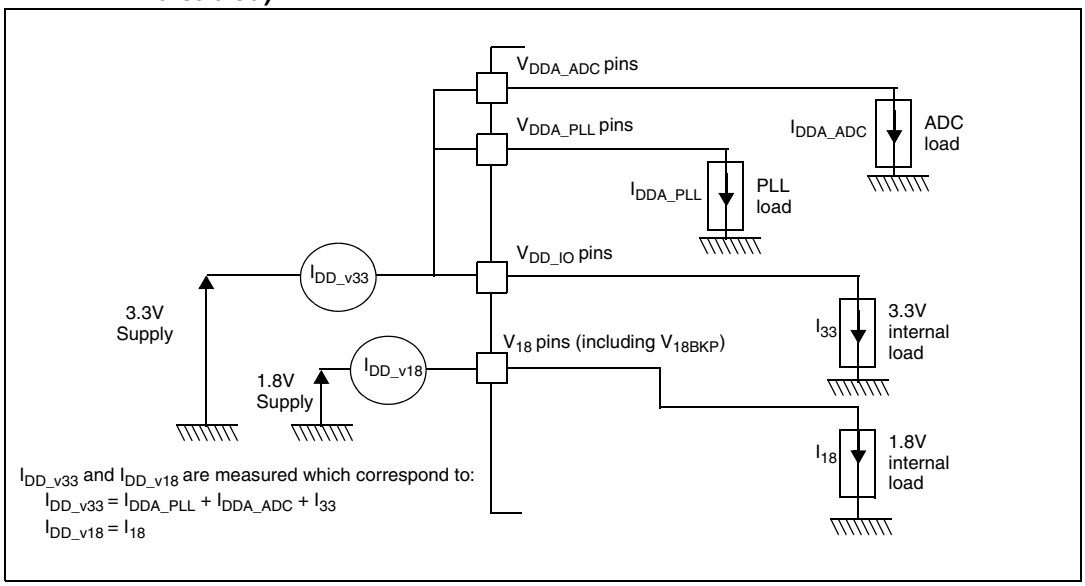


Figure 14. Power consumption measurements in power scheme 3 (regulators enabled)

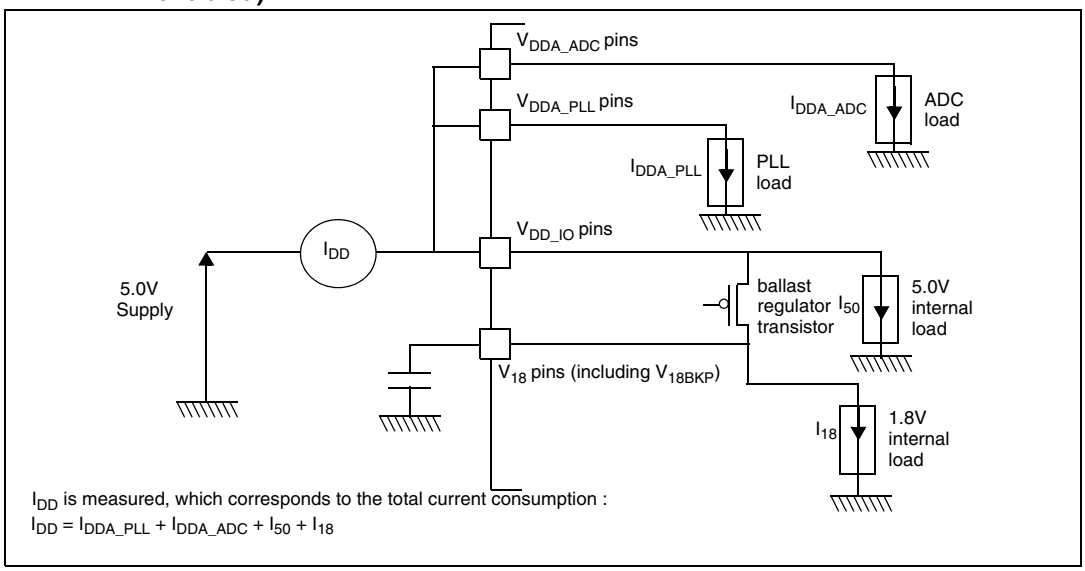
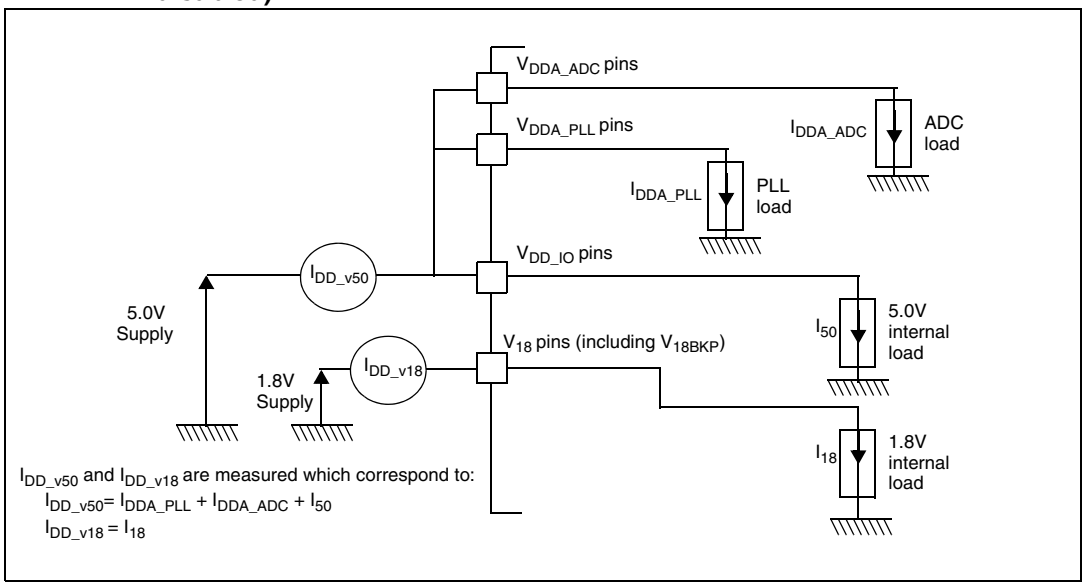


Figure 15. Power consumption measurements in power scheme 4 (regulators disabled)



6.3.2 Operating conditions at power-up / power-down

Subject to general operating conditions for T_A.

Table 11. Operating conditions at power-up / power-down

Symbol	Parameter	Conditions	Min(1)	Typ	Max(1)	Unit
t_{VDD_IO}	V_{DD_IO} rise time rate		20			µs/V
					20	ms/V
t_{V18}	V_{18} rise time rate (1)	When 1.8 V power is supplied externally	20			µs/V
					20	ms/V

1. Data guaranteed by characterization, not tested in production.

6.3.3 Embedded voltage regulators

Subject to general operating conditions for V_{DD_IO}, and T_A

Table 12. Embedded voltage regulators

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
V_{MVREG}	MVREG power supply(1)	load <150 mA	1.65	1.80	1.95	V
V_{LPVREG}	LPVREG power supply(2)	load <10 mA	1.30	1.40	1.50	V
t_{VREG_PWRUP}(1)	Voltage Regulators start-up time (to reach 90% of final V_{18} value) at V_{DD_IO} power-up(3)	V_{DD_IO} rise slope = 20 µs/V		80		µs
		V_{DD_IO} rise slope = 20 ms/V		35		ms

1. V_{MVREG} is observed on the V_{18}, V_{18REG} and V_{18BKP} pins except in the following case:
   - In STOP mode with MVREG OFF (LP_PARAM13 bit). See note 2.
   - In STANDBY mo*de. See note 2.*
2. In STANDBY mode, V_{LPVREG} is observed on the V_{18BKP} pin
   In STOP mode, V_{LPVREG} is observed on the V_{18}, V_{18REG} and V_{18BKP} pins.
3. Once V_{DD_IO} has reached 3.0 V, the RSM (Regulator Startup Monitor) generates an internal RESET during this start-up time.

Figure 16. Power consumption in STOP mode in Single supply scheme (3.3 V range)

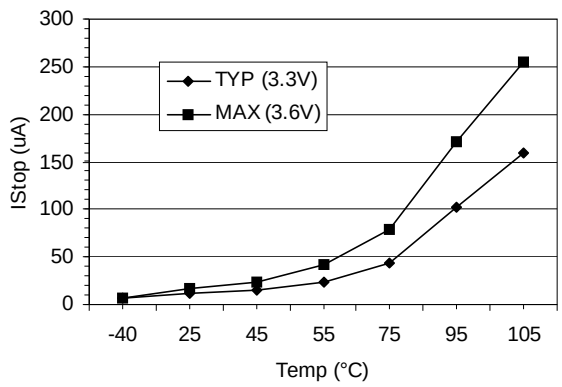


Figure 17. Power consumption in STOP mode Single supply scheme (5 V range)

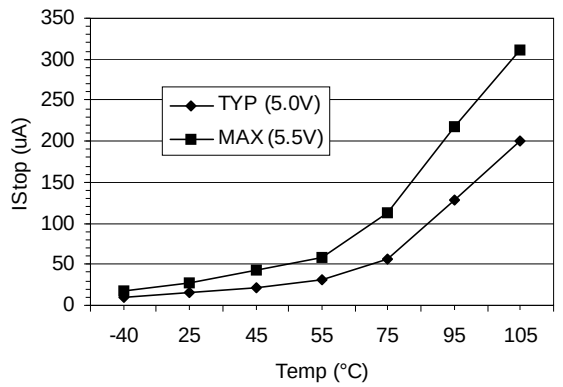


Figure 18. Power consumption in STANDBY mode (3.3 V range)

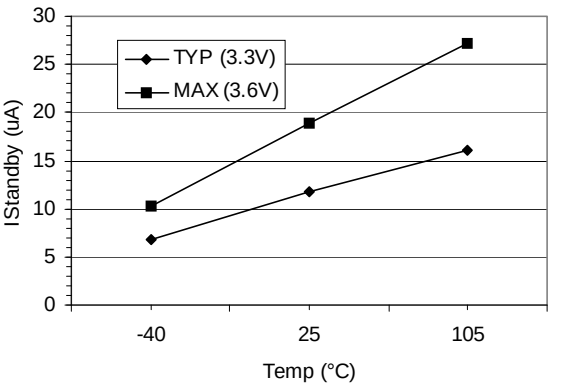


Figure 19. Power consumption in STANDBY mode (5 V range)

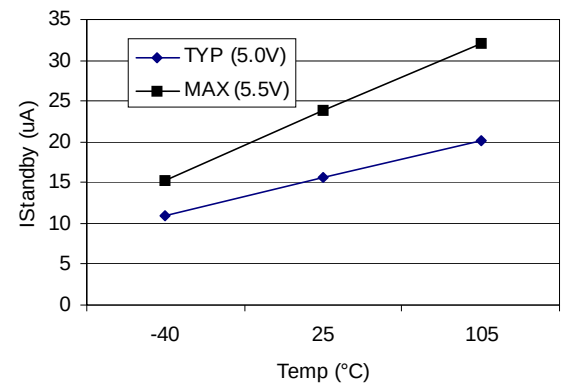


Table 16. Dual supply supply typical power consumption in Run, WFI, Slow and Slow-WFI modes

To calculate the power consumption in Dual supply mode, refer to the values given in *Table 15*. and consider that this consumption is split as follows:

$I_{DD(single\ supply)} \sim I_{DD(dual\ supply)} = I_{DD\_V18} + I_{DD(VDD\_IO)}$

For 3.3V range: $I_{DD(VDD\_IO)}$ ~ 1 to 2 mA

For 5V range: $I_{DD(VDD\_IO)}$ ~ 2 to 3 mA

Therefore most of the consumption is sunk on the V_{18} power supply

This formula does not apply in STOP and STANDBY modes, refer to *Table 17*.

Subject to general operating conditions for V_{DD_IO}, and T_A

Table 17. Typical power consumption in STOP and STANDBY modes

Symbol	Parameter	Conditions		3.3V Typ(1)	5V Typ(2)	Unit
I_{DD}(3)	Supply current in STOP mode(4)	LP_PARAM bits: ALL OFF(5)		12	15	µA
		LP_PARAM bits : MVREG ON, OSC4M OFF, FLASH OFF(6)		130	135	
		LP_PARAM bits: MVREG ON, OSC4M ON , FLASH OFF(6)		1950	1930	
		LP_PARAM bits: MVREG ON, OSC4M OFF, FLASH ON (6)		630	635	
		LP_PARAM bits: MVREG ON, OSC4M ON, FLASH ON (6)		2435	2425	
	Supply current in STOP mode(7)	LPPARAM bits: ALL OFF, with V_{18}=1.8 V	I_{DD_V18} I_{DD_V33}	5 <1	5 <1	µA
		LP_PARAM bits: OSC4M ON, FLASH OFF	I_{DD_V18} I_{DD_V33}	410 1475	410 1435	
		LP_PARAM bits: OSC4M OFF, FLASH ON	I_{DD_V18} I_{DD_V33}	550 <1	550 1	
		LP_PARAM bits: OSC4M ON, FLASH ON	I_{DD_V18} I_{DD_V33}	910 1475	910 1445	
	Supply current in STANDBY mode(4)	RTC OFF		11	14	µA
		RTC ON clocked by OSC32K		14	18	

1. Typical data are based on T_A=25°C, V_{DD_IO}=3.3 V and V_{18}=1.8 V unless otherwise indicated in the table.
2. Typical data are based on T_A=25°C, V_{DD_IO}=5.0 V and V_{18}=1.8 V unless otherwise indicated in the table.
3. The conditions for these consumption measurements are described at the beginning of *Section 6.3.4 on page 36*.
4. Single supply scheme see *Figure 12*.
5. In this mode, the whole digital circuitry is powered internally by the LPVREG at approximately 1.4 V, which significantly reduces the leakage currents.
6. In this mode, the whole digital circuitry is powered internally by the MVREG at 1.8 V.
7. Dual supply scheme see *Figure 13*.

OSC32K crystal / ceramic resonator oscillator

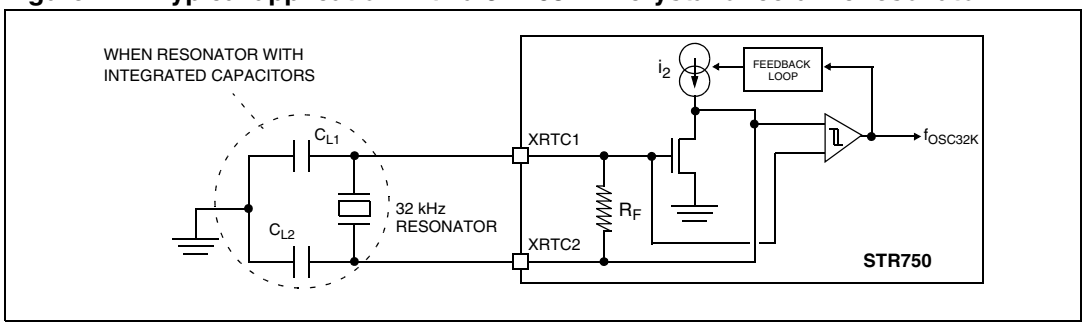
The STR7 RTC clock can be supplied with a 32.768 kHz Crystal/Ceramic resonator oscillator. All the information given in this paragraph are based on product characterisation with specified typical external components. In the application, the resonator and the load capacitors have to be placed as close as possible to the oscillator pins in order to minimize output distortion and start-up stabilization time. Refer to the crystal/ceramic resonator manufacturer for more details (frequency, package, accuracy...).

Table 23. OSC32K crystal / ceramic resonator oscillator

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
f_{OSC32K}	Oscillator Frequency			32.768		kHz
R_F	Feedback resistor	V_{DD_IO}=3.3 V or 5.0 V	270	310	370	kΩ
C_{L1} C_{L2}	Recommended load capacitance versus equivalent serial resistance of the crystal or ceramic resonator (R_S)(1)	R_S=40KΩ		12.5	15	pF
i_2	XT2 driving current	V_{DD_IO}=3.3 V or 5.0 V V_{IN}=V_{SS}	1		5	µA
$t_{SU(OSC32K)}$(2)	Startup time	V_{DD_IO} is stabilized		2.5		s

1. The oscillator selection can be optimized in terms of supply current using an high quality resonator with small R_S value. Refer to crystal/ceramic resonator manufacturer for more details
2. $t_{SU(OSC32K)}$ is the start-up time measured from the moment it is enabled (by software) to a stabilized 32 kHz oscillation is reached. This value is measured for a standard crystal resonator and it can vary significantly with the crystal/ceramic resonator manufacturer

Figure 22. Typical application with a 32.768 kHz crystal or ceramic resonator



PLL characteristics

PLL Jitter Terminology

- Self-referred single period jitter (period jitter)

  Period Jitter is defined as the difference of the maximum period (T_{max}) and minimum period (T_{min}) at the output of the PLL where T_{max} is the maximum time difference between 2 consecutive clock rising edges and T_{min} is the minimum time difference between 2 consecutive clock rising edges.

  See *Figure 23*

- Self-referred long term jitter (N period jitter)

  Self-referred long term Jitter is defined as the difference of the maximum period (T_{max}) and minimum period (T_{min}) at the output of the PLL where T_{max} is the maximum time

Electro magnetic interference (EMI)

Based on a simple application running on the product (toggling 2 LEDs through the I/O ports), the product is monitored in terms of emission. This emission test is in line with the norm SAE J 1752/3 which specifies the board and the loading of each pin.

Table 29. EMI characteristics

Symbol	Parameter	Conditions	Monitored Frequency Band	Max vs. [f_{OSC4M}/f_{HCLK}]		Unit
				4/32MHz	4/60MHz	
S_{EMI}	Peak level	Flash devices: V_{DD_IO}=3.3 V or 5 V, T_A=+25° C, LQFP64 package conforming to SAE J 1752/3	0.1 MHz to 30 MHz	22	26	dBµV
			30 MHz to 130 MHz	31	26	
			130 MHz to 1 GHz	19	23	
			SAE EMI Level	>4	>4	-

Absolute maximum ratings (electrical sensitivity)

Based on three different tests (ESD, LU and DLU) using specific measurement methods, the product is stressed in order to determine its performance in terms of electrical sensitivity. For more details, refer to the application note AN1181.

Electro-Static discharge (ESD)

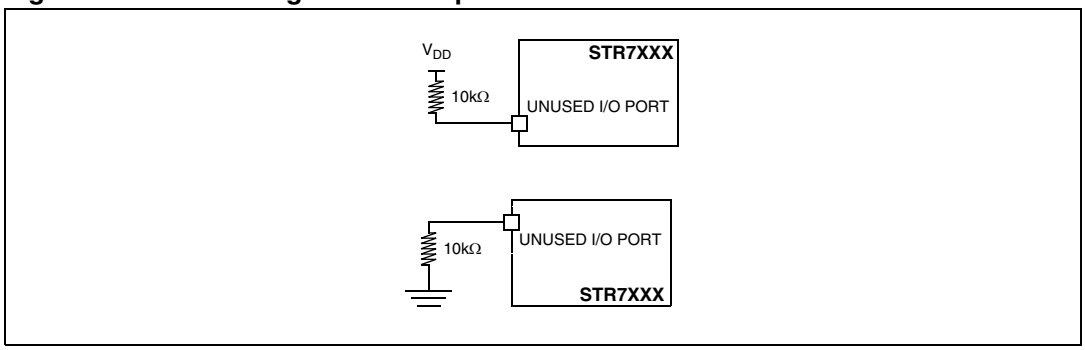
Electro-Static Discharges (a positive then a negative pulse separated by 1 second) are applied to the pins of each sample according to each pin combination. The sample size depends on the number of supply pins in the device (3 parts*(n+1) supply pin). Two models can be simulated: Human Body Model and Machine Model. This test conforms to the JESD22-A114A/A115A standard.

Table 30. Absolute maximum ratings

Symbol	Ratings	Conditions	Maximum value(1)	Unit
$V_{ESD(HBM)}$	Electro-static discharge voltage (Human Body Model)	T_A=+25° C	2000	V
$V_{ESD(MM)}$	Electro-static discharge voltage (Machine Model)		200	
$V_{ESD(CDM)}$	Electro-static discharge voltage (Charge Device Model)		750	

1. Data based on product characterisation, not tested in production.

Figure 25. Connecting unused I/O pins



Output driving current

The GP I/Os have different drive capabilities:

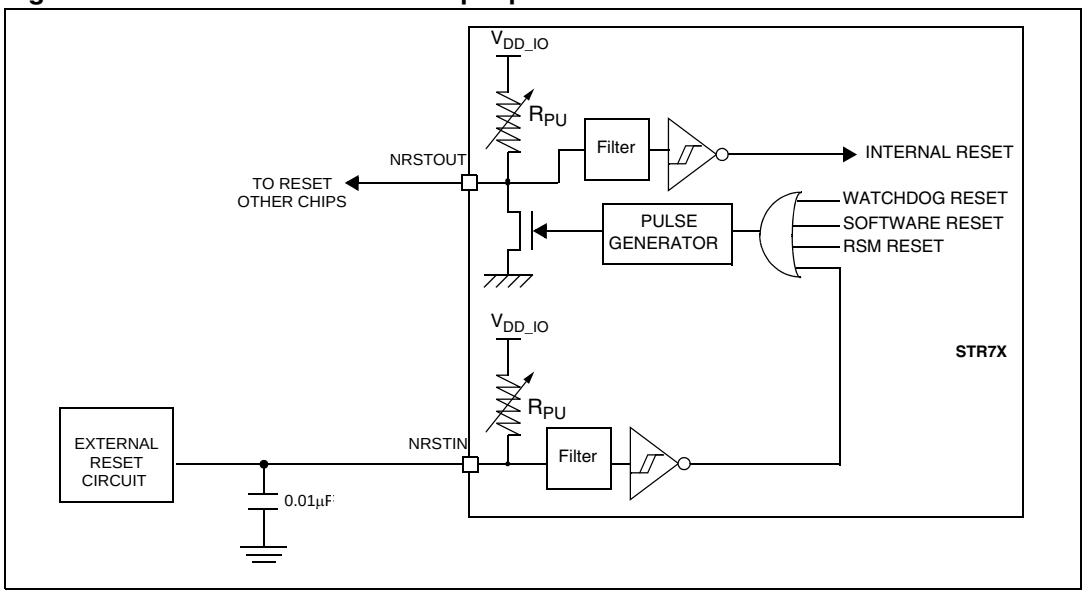
- O2 outputs can sink or source up to +/-2 mA.
- O4 outputs can sink or source up to +/-4 mA.
- outputs can sink or source up to +/-8 mA or can sink +20 mA (with a relaxed V_{OL}).

In the application, the user must limit the number of I/O pins which can drive current to respect the absolute maximum rating specified in *Section 6.2.2* :

- The sum of the current sourced by all the I/Os on $V_{DD\_IO,}$ plus the maximum RUN consumption of the MCU sourced on $V_{DD\_IO,}$ can not exceed the absolute maximum rating IV_{DD_IO}.
- The sum of the current sunk by all the I/Os on V_{SS_IO} plus the maximum RUN consumption of the MCU sunk on V_{SS_IO} can not exceed the absolute maximum rating IV_{SS_IO}.

Subject to general operating conditions for V_{DD_IO} and T_A unless otherwise specified.

Figure 27. Recommended NRSTIN pin protection



1. The user must ensure that the level on the NRSTIN pin can go below the $V_{IL(NRSTIN)}$ max. level specified in *NRSTIN and NRSTOUT pins on page 58*. Otherwise the reset will not be taken into account internally.

6.3.9 TB and TIM timer characteristics

Subject to general operating conditions for V_{DD_IO}, f_{CK_SYS}, and T_A unless otherwise specified.

Refer to *Section 6.3.8: I/O port pin characteristics on page 54* for more details on the input/output alternate function characteristics (output compare, input capture, external clock, PWM output...).

Table 36. TB and TIM timers

Symbol	Parameter	Conditions		Min	Typ	Max	Unit
$t_{w(ICAP)in}$	Input capture pulse time	TIM0,1,2		2			t_{CK_TIM}
$t_{res(TIM)}$	Timer resolution time(1)	TB	$f_{CK\_TIM(MAX)} = f_{CK\_SYS}$	1			t_{CK_TIM}
			$f_{CK\_TIM} = f_{CK\_SYS}$ = 60 MHz	16.6(1)			ns
		TIM0,1,2	$f_{CK\_TIM(MAX)} = f_{CK\_SYS}$	1			t_{CK_TIM}
			$f_{CK\_TIM} = f_{CK\_SYS}$ = 60MHz	16.6(1)			ns
f_{EXT}	Timer external clock frequency on TI1 or TI2	TIM0,1,2	$f_{CK\_TIM(MAX)} = f_{CK\_SYS}$	0		$f_{CK\_TIM}/4$	MHz
			$f_{CK\_TIM} = f_{CK\_SYS}$ = 60 MHz	0		15	MHz
Res_{TIM}	Timer resolution					16	bit
$t_{COUNTER}$	16-bit Counter clock period when internal clock is selected (16-bit Prescaler)	TB		1		65536	t_{CK_TIM}
			$f_{CK\_TIM} = f_{CK\_SYS}$ = 60 MHz	0.0166		1092	µs
		TIM0,1,2		1		65536	t_{CK_TIM}
			$f_{CK\_TIM} = f_{CK\_SYS}$ = 60 MHz	0.0166		1092	µs
t_{MAX_COUNT}	Maximum Possible Count	TB				65536x65536	t_{CK_TIM}
			$f_{CK\_TIM} = f_{CK\_SYS}$ = 60 MHz			71.58	s
		TIM0,1,2				65536x65536	t_{CK_TIM}
			$f_{CK\_TIM} = f_{CK\_SYS}$ = 60 MHz			71.58	s

1. Take into account the frequency limitation due to the I/O speed capability when outputting the PWM to I/O pin, described in *: Output speed on page 57*.

Figure 28. SPI configuration - master mode, single transfer

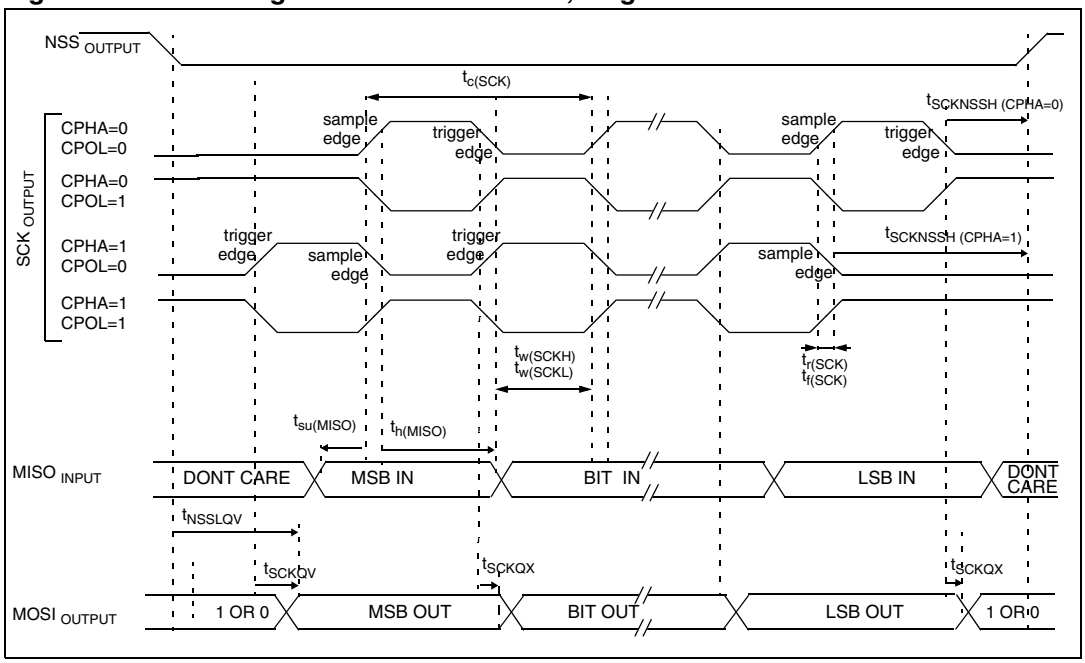


Figure 29. SPI configuration - master mode, continuous transfer, CPHA=0

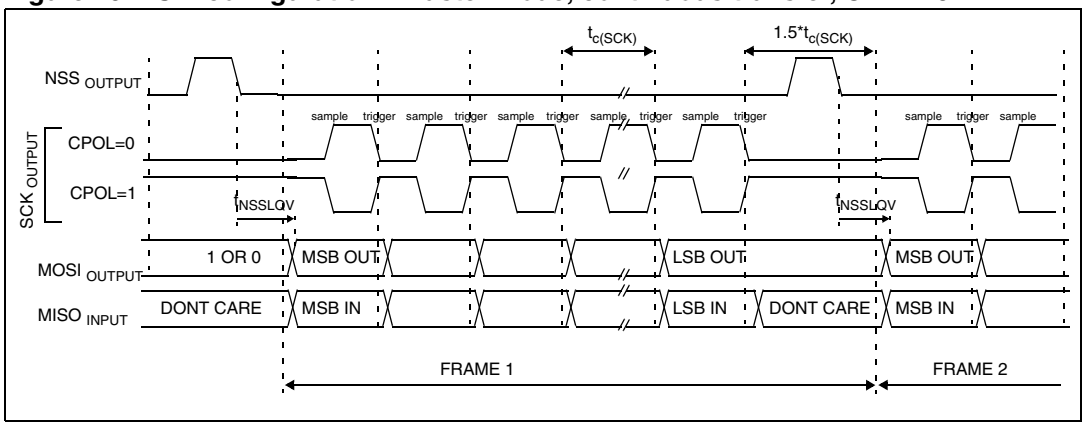


Figure 30. SPI configuration - master mode, continuous transfer, CPHA=1

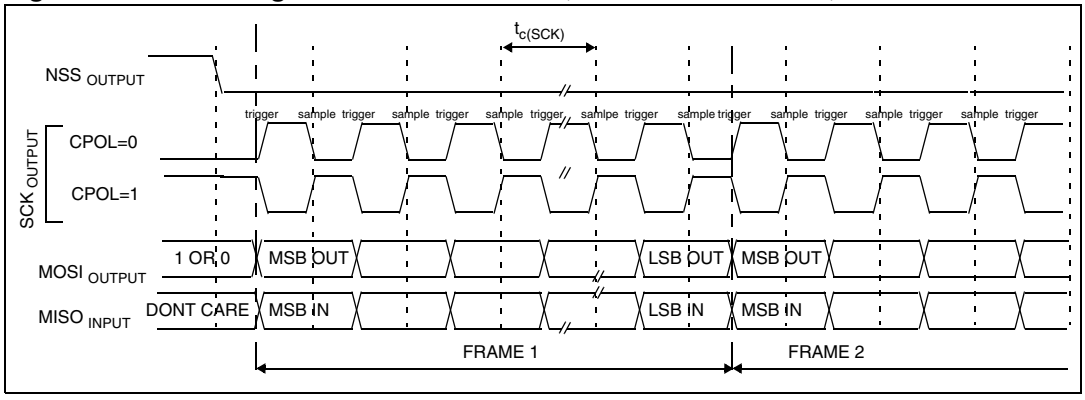


Figure 37. TI configuration - slave mode, single transfer

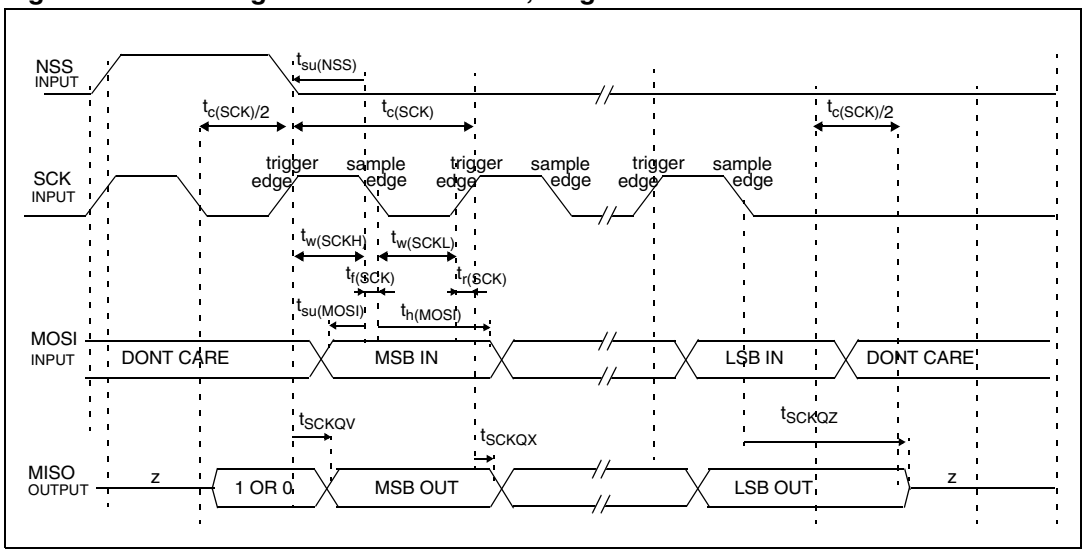
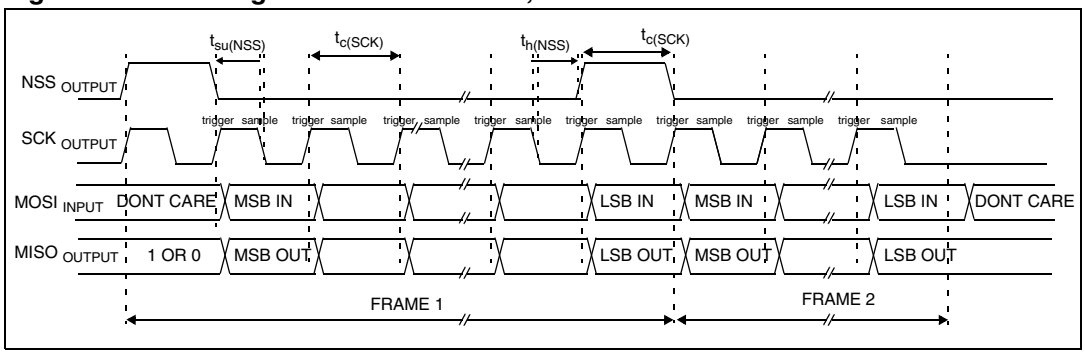


Figure 38. TI configuration - slave mode, continuous transfer



SMI - serial memory interface

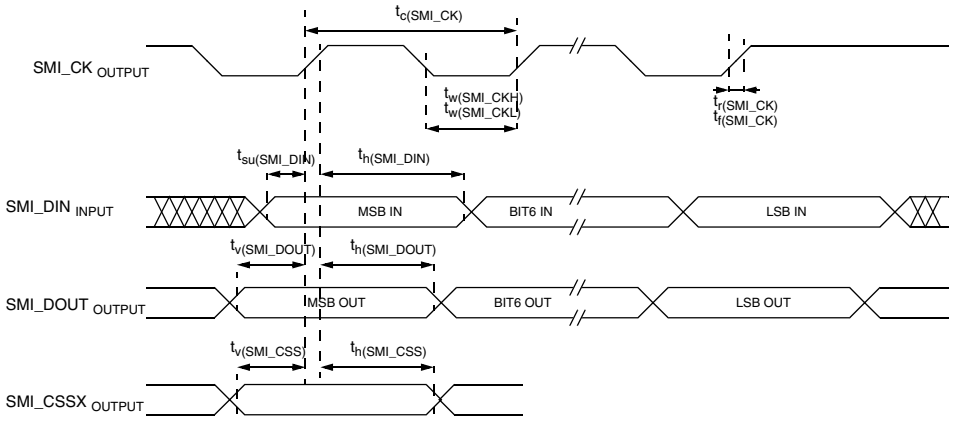
Subject to general operating conditions with $C_L \approx 30$ pF.

Table 40. SMI characteristics(1)

Symbol	Parameter	Min	Max	Unit
f_{SMI_CK}	SMI clock frequency		32(2)(3)	MHz
			48(4)	
$t_{r(SMI\_CK)}$	SMI clock rise time		10	ns
$t_{f(SMI\_CK)}$	SMI clock fall time		8	
$t_{v(SMI\_DOUT)}$	Data output valid time		10	
$t_{h(SMI\_DOUT)}$	Data output hold time		0	
$t_{v(SMI\_CSSx)}$	CSS output valid time		10	
$t_{h(SMI\_CSSx)}$	CSS output hold time		0	
$t_{su(SMI\_DIN)}$	Data input setup time	0		
$t_{h(SMI\_DIN)}$	Data input hold time	5		

1. Data based on characterisation results, not tested in production.
2. Max. frequency = $f_{PCLK}/2 = 64/2 = 32$ MHz.
3. Valid for all temperature ranges: -40 to 105 °C, with 30 pF load capacitance.
4. Valid up to 60 °C, with 10 pF load capacitance.

Figure 39. SMI timing diagram



I²C - Inter IC control interface

Subject to general operating conditions for V_{DD_IO}, f_{PCLK}, and T_A unless otherwise specified.

The I²C interface meets the requirements of the Standard I²C communication protocol described in the following table with the restriction mentioned below:

Restriction: The I/O pins which SDA and SCL are mapped to are not “True” Open-Drain: when configured as open-drain, the PMOS connected between the I/O pin and V_{DD_IO} is disabled, but it is still present. Also, there is a protection diode between the I/O pin and V_{DD_IO}. Consequently, when using this I²C in a multi-master network, it is

Table 44. USB: Full speed electrical characteristics

Symbol	Parameter	Conditions	Min	Max	Unit
t_{rfm}	Rise/ Fall Time matching	t_r/t_f	90	110	%
V_{CRS}	Output signal Crossover Voltage		1.3	2.0	V

1. Measured from 10% to 90% of the data signal. For more detailed informations, please refer to USB Specification - Chapter 7 (version 2.0).

7.2 Thermal characteristics

The maximum chip junction temperature (T_{Jmax}) must never exceed the values given in *Table 10: General operating conditions on page 34*.

The maximum chip-junction temperature, T_{Jmax}, in degrees Celsius, may be calculated using the following equation:

$$T_{Jmax} = T_{Amax} + (P_{Dmax} \times \Theta_{JA})$$

Where:

- T_{Amax} is the maximum Ambient Temperature in °C,
- Θ_{JA} is the Package Junction-to-Ambient Thermal Resistance, in ° C/W,
- P_{Dmax} is the sum of P_{INTmax} and $P_{I/Omax}$ ($P_{Dmax} = P_{INTmax} + P_{I/Omax}$),
- P_{INTmax} is the product of I_{DD} and V_{DD}, expressed in Watts. This is the maximum chip internal power.
- $P_{I/Omax}$ represents the maximum Power Dissipation on Output Pins.
  Where:
  $P_{I/Omax} = \Sigma (V_{OL}*I_{OL}) + \Sigma((V_{DD}-V_{OH})*I_{OH})$,
  taking into account the actual V_{OL} / I_{OL} and V_{OH} / I_{OH} of the I/Os at low and high level in the application.

Table 48. Thermal characteristics(1)

Symbol	Parameter	Value	Unit
Θ_{JA}	**Thermal Resistance Junction-Ambient** LQFP 100 - 14 x 14 mm / 0.5 mm pitch	46	°C/W
Θ_{JA}	**Thermal Resistance Junction-Ambient** LQFP 64 - 10 x 10 mm / 0.5 mm pitch	45	°C/W
Θ_{JA}	**Thermal Resistance Junction-Ambient** LFBGA 64 - 8 x 8 x 1.7mm	58	°C/W
Θ_{JA}	**Thermal Resistance Junction-Ambient** LFBGA 100 - 10 x 10 x 1.7mm	41	°C/W

1. Thermal resistances are based on JEDEC JESD51-2 with 4-layer PCB in a natural convection environment.

7.2.1 Reference document

JESD51-2 Integrated Circuits Thermal Test Method Environment Conditions - Natural Convection (Still Air). Available from www.jedec.org

7.2.2 Selecting the product temperature range

When ordering the microcontroller, the temperature range is specified in the order code *Table 49: Order codes on page 81*.

The following example shows how to calculate the temperature range needed for a given application.

Assuming the following application conditions:

Maximum ambient temperature T_{Amax}= 82 °C (measured according to JESD51-2), I_{DDmax}=8 mA, V_{DD} = 5 V, maximum 20 I/Os used at the same time in output at low level with I_{OL} = 8 mA, V_{OL}= 0.4 V

$$P_{INTmax} = 8 \text{ mA} \times 5 \text{ V} = 400 \text{ mW}$$

$$P_{IOmax} = 20 \times 8 \text{ mA} \times 0.4\text{V} = 64 \text{ mW}$$

This gives: P_{INTmax}= 400 mW and P_{IOmax} 64 mW:

$$P_{Dmax} = 400 \text{ mW} + 64 \text{ mW}$$

Thus: P_{Dmax} = 464 mW

Using the values obtained in *Table 48* T_{Jmax} is calculated as follows:

– For LQFP100, 46°C/W

T_{Jmax} = 82° C + (46° C/W x 464 mW) = 82°C + 21°C = 103° C

This is within the range of the suffix 6 version parts (-40 < T_J < 105° C).

In this case, parts must be ordered at least with the temperature range suffix 6 (see *Table 49: Order codes on page 81*).

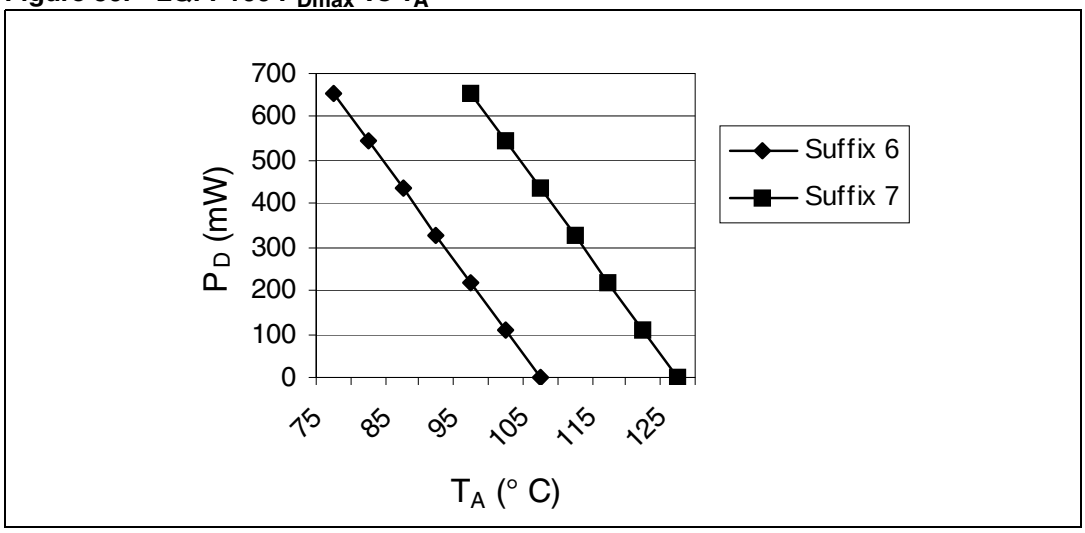
– For BGA64, 58°C/W

T_{Jmax} = 82° C + (58° C/W x 464 mW) = 82°C + 27°C = 109° C

This is within the range of the suffix 7 version parts (-40 < T_J < 125° C).

In this case, parts must be ordered at least with the temperature range suffix 7 (see *Table 49: Order codes on page 81*).

Figure 50. LQFP100 P_{Dmax} vs T_A



8 Order codes

Table 49. Order codes

Order code	Flash Prog. Memory (Bank 0) Kbytes	Package	CAN Periph	USB Periph	Nominal Temp. Range (T_A)
STR750FV0T6	64	LQFP100 14x14	Yes	Yes	-40 to +85°C
STR750FV1T6	128				
STR750FV2T6	256				
STR750FV0H6	64	LFBGA100 10x10			
STR750FV1H6	128				
STR750FV2H6	256				
STR751FR0T6	64	LQFP64 10x10	-	Yes	-40 to +85°C
STR751FR1T6	128				
STR751FR2T6	256				
STR751FR0H6	64	LFBGA64 8x8			
STR751FR1H6	128				
STR751FR2H6	256				
STR752FR0T6	64	LQFP64 10x10	Yes	-	-40 to +85°C
STR752FR1T6	128				
STR752FR2T6	256				
STR752FR0H6	64	LFBGA64 8x8			
STR752FR1H6	128				
STR752FR2H6	256				
STR752FR0T7	64	LQFP64 10x10	Yes	-	-40 to +105°C
STR752FR1T7	128				
STR752FR2T7	256				
STR752FR0H7	64	LFBGA64 8x8			
STR752FR1H7	128				
STR752FR2H7	256				
STR755FR0T6	64	LQFP64 10x10	-	-	-40 to +85°C
STR755FR1T6	128				
STR755FR2T6	256				
STR755FR0H6	64	LFBGA64 8x8			
STR755FR1H6	128				
STR755FR2H6	256				

9 Revision history

Table 50. Document revision history

Date	Revision	Description of Changes
25-Sep-2006	1	Initial release
30-Oct-2006	2	Added power consumption data for 5V operation in *Section 6*
04-Jul-2007	3	Changed datasheet title from STR750F to STR750FXX STR751Fxx STR752Fxx STR755xx. Added *Table 1: Device summary on page 1* Added note 1 to *Table 6* Added STOP mode IDD max. values in *Table 14* Updated XT2 driving current in *Table 23.* Updated RPD in *Table 32* Updated *Table 21: XRTC1 external clock source on page 45* Updated *Table 34: Output speed on page 57* Added characteristics for *SSP synchronous serial peripheral in master mode (SPI or TI mode) on page 62* and *SSP synchronous serial peripheral in slave mode (SPI or TI mode) on page 65* Added characteristics for *SMI - serial memory interface on page 68* Added *Table 42: USB startup time on page 70*
23-Oct-2007	4	Updated *Section 6.2.3: Thermal characteristics on page 33* Updated P_D, T_J and T_A in *Section 6.3: Operating conditions on page 34* Updated *Table 20: XT1 external clock source on page 44* Updated *Table 21: XRTC1 external clock source on page 45* Updated *Section 7: Package characteristics on page 76* (inches rounded to 4 decimal digits instead of 3) Updated Ordering information *Section 8: Order codes on page 81*
17-Feb-2009	5	Modified note 3 below *Table 8: Current characteristics on page 33* Added AHB clock frequency for write access to Flash registers in *Table 10: General operating conditions on page 34* Modified note 3 below *Table 41: SDA and SCL characteristics on page 69*